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				First Named Inventor	Misao TAKAKUSAKI
				Art Unit	1792
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Sheet	1	of	1	Attorney Docket Number	1592-0159PUS1

U.S. PATENT DOCUMENTS					
Examiner Initials*	Cite No. ¹	Document Number Number-Kind Code ² (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear

FOREIGN PATENT DOCUMENTS					
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NON PATENT LITERATURE DOCUMENTS					
Examiner Initials	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published			T ²
	CA	MI et al., "Improvement of optical and electronic properties in broken gap mid-wave infrared laser materials," Conference on Lasers and Electro-Optics (CLEO 2001), Technical Digest, Postconference Edition, Baltimore, Md., May 6-11, 2001 [Trends in Optics and Photonics. (Tops)], US Washington, WA: OSA, US, Vol. 56, pp. 486-487, XP010560097			
	CB	HARPER et al., "Cross-sectional scanning tunneling microscopy characterization of molecular beam epitaxy grown InAs/GaSb/AISb heterostructures for mid-infrared interband cascade lasers," Journal of Vacuum Science & Technology B: Microelectronicsprocessing and Phenomena, American Vacuum Society, New York, NY, US, Vol. 16, No. 3, May 1, 1998, pg. 1389-1394, XP012006832			
	CC	HASENBERG et al., "Molecular beam epitaxy growth and characterization of broken-gap (type II) superlattices and quantum wells for midwave-infrared laser diodes," Journal of Vacuum Science & Technology B: Microelectronicsprocessing and Phenomena, American Vacuum Society, New York, NY, US, Vol. 18, No. 3, May 1, 2000, pp. 1623-1627, XP012006258			
	CD	DESLALVO et al., "Citric Acid Etching of GaAs _{1-x} Sb _x , Al _{0.5} Ga _{0.5} Sb, and InAs for Heterostructure Device Fabrication," Journal of the Electrochemical Society, Electrochemical Society, Manchester, New Hampshire, US, Vol. 141, No. 12, December 1, 1994, pp. 3526-3531, XP000495786			

Examiner Signature	Date Considered
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